II Year II Semester

Code:20IO4707

ELECTRONIC DEVICES (Minors)

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Course Objectives:

- 1. To learn and understand the basic concepts of semiconductor physics and working of a Diode with its applications.
- 2. To study the physical phenomena such as conduction, transport mechanism and electrical characteristics of different diodes.
- 3. To acquire knowledge about the principle, working and operation of Bipolar Junction Transistor and purpose of its biasing techniques.
- 4. To acquire knowledge about the principle, working and operation of FETs and purpose of its biasing techniques.
- 5. To understand the working, analysis and design of transistor amplifier circuits at low frequencies

Course Outcomes:

A student who successfully fulfils this course requirement will be having:

- 1. An ability to apply the basic concepts of semiconductor and to understand the formation and characteristics of PN Junction Diode with relevant applications
- 2. An ability to understand the Construction, Operation, Characteristics and applications of special diodes
- 3. An ability to illustrate the construction, principle of operation, Characteristics of BJT with its biasing techniques.
- 4. An ability to know the Construction, Characteristics of FET & MOSFET with their biasing techniques
- 5. An ability to perform the analysis of small signal low frequency transistor amplifier circuits using BJT and FET in different configurations.

UNIT-I

Semiconductor Basics & PN Junction Diode

Atomic Structure, Semiconductors, conductors and Insulators, Covalent Bonds, Conduction in Semiconductors, N-Type and P-Type Semiconductors, The diode, Biasing a diode, Voltage-Current Characteristic of a diode, Diode Models, Testing a diode, Diode Applications – Half-Wave Rectifiers, Full-Wave Rectifiers, Power supply filters and regulators

UNIT-II

Special Diodes

Breakdown Mechanisms – Zener Breakdown and Avalanche Breakdown, Zener Diode V-I Characteristics, Zener diode as voltage regulator. Construction, Operation, Characteristics and applications of Varactor Diode, LED, SCR, The Schottky diode, The PIN diode, The Tunnel Diode, The Laser Diode, LCD

UNIT-III

Bipolar Junction Transistors

Transistor Structure, Basic Transistor Operation, Transistor Characteristics and parameters, The

Transistor as an Amplifier, The Transistor as a switch, Transistor Packages and Terminal Identification, BJT Bias Circuits – The DC operating point, Voltage divider Bias, Base Bias, Emitter Bias, Collector-Feedback Bias

UNIT-IV

Field Effect Transistors

The JFET, JFET Characteristics and Parameters, JFET Biasing – Self Bias, Voltage divider Bias. The MOSFET – Depletion MOSFET, Enhancement MOSFET. MOSFET Characteristics and Parameters, MOSFET Biasing – D-MOSFET Bias, E-MOSFET Bias.

UNIT-V

Transistor Amplifier circuits

BJT: Two port network, Transistor hybrid model, determination of h-parameters, conversion of h-parameters, generalized analysis of transistor amplifier model using h-parameters, Analysis of CB, CE and CC amplifiers using exact and approximate analysis, comparison of transistor amplifiers. **FET:** Generalized analysis of small signal model of FET, Analysis of CG, CS and CD amplifiers, comparison of FET amplifiers.

Text Books:

- 1. Electronic Devices Thomas L. Floyd, Pearson Education, Seventh Edition, 2005.
- 2. Electronic Devices and Circuits S.Salivahanan, N.Suresh Kumar, McGraw Hill, Third Edition, 2010.

Reference Books:

- 1. Electronics Devices & Circuit Theory Robert L.Boylestad and Louis Nashelsky, Prentice Hall, Tenth Edition, 2009.
- 2. Electronic Devices and Circuits J. Millman and C. Halkias, Tata McGraw Hill, Second Edition, 2007.